CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor laser device which emits light at an oscillation wavelength, the laser device comprising~~:~~ a reflective film ~~constituted of~~ including a multilayer dielectric ~~films~~ film, ~~being provided~~ on at least one side of optical exit ~~faces~~ face of a laser chip~~;~~, wherein the reflective film includes, in sequence from a side in contact with the laser chip, a first dielectric film of a refractive index n1, a second dielectric film of a refractive index n2, a third dielectric film of a refractive index n3, and a fourth dielectric film of a refractive index n4, and ~~each of refractive indices satisfies a relation:~~ $n2 = n4 < n1 < n3$.

2. (Currently Amended) A semiconductor laser device which emits light at an oscillation wavelength, the laser device comprising~~:~~ a reflective film ~~constituted of~~ including a multilayer dielectric ~~films~~ film, ~~being provided~~ on at least one side of optical exit faces of a laser chip~~;~~, wherein the reflective film includes, in sequence from a side in contact with the laser chip, a first dielectric film of a refractive index n1, a second dielectric film of a refractive index n2, a third dielectric film of a refractive index n3, and a fourth dielectric film of a refractive index n4, and ~~each of refractive indices satisfies a relation:~~ $n2 = n4 < n3 < n1$.

3. (Currently Amended) The semiconductor laser device according to Claim 1, wherein each ~~thickness~~ of the first ~~to~~, second, third, and fourth dielectric films ~~is set up~~ has a thickness, in terms of optical length, within ±30% ~~of range~~ of a thickness ~~of~~ that is an ~~integral~~ integer multiple of 1/4 of the oscillation wavelength of the semiconductor laser device.

4. (Currently Amended) The semiconductor laser device according to Claim 2, wherein each ~~thickness~~ of the first ~~to~~, second, third, and fourth dielectric films ~~is set up~~ has a thickness, in terms of optical length, within ±30% ~~of range~~ of a thickness ~~of~~ that is an ~~integral~~ integer multiple of 1/4 of the oscillation wavelength of the semiconductor laser device.

5. (Currently Amended) A semiconductor laser device which emits light of an oscillation wavelength λ, comprising:

a reflective film ~~constituted of~~ including a multilayer dielectric ~~films~~ film, ~~being provided~~ on at least one side of optical exit faces of a laser chip~~;~~, wherein

the reflective film ~~having~~ has a reflectance of 3% to 15% and includes, in sequence from a side in contact with the laser chip, a first dielectric film of a refractive index n1 and a thickness d1, a second dielectric film of a refractive index n2 and a thickness d2, a

third dielectric film of a refractive index n3 and a thickness d3, and a fourth dielectric film of a refractive index n4 and a thickness d4, ~~and~~

the refractive index n1 satisfies $1.6 < n1 \leq 1.9$, the refractive index n2 satisfies $1.3 \leq n2 \leq 1.6$, the refractive index n3 satisfies $1.9 < n3 \leq 2.3$, and the refractive index n4 satisfies $1.3 \leq n4 \leq 1.6$, and

the thickness d1 is substantially equal to $(2*h + 1)\lambda/(4*n1)$, the thickness d2 is substantially equal to $(2*i + 1)\lambda/(4*n2)$, the thickness d3 is substantially equal to $(2*j + 1)\lambda/(4*n3)$, and the thickness d4 is substantially equal to $(2*k + 1)\lambda/(4*n4)$, ~~wherein~~ and each of h, i, j, and k is zero or ~~more~~ a positive integer.

6. (Currently Amended) A semiconductor laser device which emits light of an oscillation wavelength λ, the laser device comprising:

a reflective film ~~constituted of~~ including a multilayer dielectric ~~films~~ film, ~~being provided~~ on at least one side of optical exit faces of a laser chip~~s~~, wherein

the reflective film ~~having~~ has a reflectance of 3% to 15% and includes, in sequence from a side in contact with the laser chip, a first dielectric film of a refractive index n1 and a thickness d1, a second dielectric film of a refractive index n2 and a thickness d2, a third dielectric film of a refractive index n3 and a thickness d3, and a fourth dielectric film of a refractive index n4 and a thickness d4, ~~and~~

the refractive index n1 satisfies $1.9 < n1 \leq 2.3$, the refractive index n2 satisfies $1.3 \leq n2 \leq 1.6$, the refractive index n3 satisfies $1.6 < n3 \leq 1.9$, and the refractive index n4 satisfies $1.3 \leq n4 \leq 1.6$, and

the thickness d1 is substantially equal to $(2*h + 1)\lambda/(4*n1)$, the thickness d2 is substantially equal to $(2*i + 1)\lambda/(4*n2)$, the thickness d3 is substantially equal to $(2*j + 1)\lambda/(4*n3)$, and the thickness d4 is substantially equal to $(2*k + 1)\lambda/(4*n4)$, ~~wherein~~ each of h, i, j, and k is zero or ~~more~~ a positive integer.

7. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the first dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3, the second and fourth dielectric films are ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2, and the third dielectric film is ~~formed of either~~ selected from the group consisting of Ta_2O_5, SiO, ZrO_2, ZnO, TiO, TiO_2, ZnS, Nb_2O_5, HfO_2, and AlN.

8. (Currently Amended) The semiconductor laser device according to Claim 5, wherein the first dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3, the second and fourth dielectric films are ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2, and the third dielectric film is ~~formed of either~~ selected from the group consisting of Ta_2O_5, SiO, ZrO_2, ZnO, TiO, TiO_2, ZnS, Nb_2O_5, HfO_2, and AlN.

9. (Currently Amended) The semiconductor laser device according to Claim 2, wherein the first dielectric film is ~~formed of either~~ selected from the group consisting of Ta_2O_5, SiO, ZrO_2, ZnO, TiO, TiO_2, ZnS, Nb_2O_5, HfO_2, and AlN, the second and fourth dielectric films are ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2, and the third dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3.

10. (Currently Amended) The semiconductor laser device according to Claim 6, wherein the first dielectric film is ~~formed of either~~ selected from the group consisting of Ta_2O_5, SiO, ZrO_2, ZnO, TiO, TiO_2, ZnS, Nb_2O_5, HfO_2, and AlN, the second and fourth dielectric films are ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2, and the third dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3.

11. (Currently Amended) The semiconductor laser device according to Claim 1, ~~wherein a multilayer dielectric film in combination with~~ including a fifth dielectric film and a sixth dielectric film ~~is additionally formed~~ in a region other than a light emitting point on ~~the~~ optical exit faces of the laser chip, and ~~a~~ reflectance of the region other than the light emitting point is smaller than ~~a~~ reflectance of the region of the light emitting point.

12. (Currently Amended) The semiconductor laser device according to Claim 2, ~~wherein a multilayer dielectric film in combination with~~ including a fifth dielectric film and a sixth dielectric film ~~is additionally formed~~ in a region other than a light emitting point on ~~the~~ optical exit faces of the laser chip, and ~~a~~ reflectance of the region other than the light emitting point is smaller than ~~a~~ reflectance of the region of the light emitting point.

13. (Currently Amended) The semiconductor laser device according to Claim 11, wherein each ~~thickness~~ of the fifth and sixth dielectric films ~~is set up~~ has a thickness, in terms

of optical length, within ±30% of range of ~~a thickness of~~ an integral multiple of 1/4 of the oscillation wavelength of the semiconductor laser device.

14. (Currently Amended) The semiconductor laser device according to Claim 12, wherein each ~~thickness~~ of the fifth and sixth dielectric films ~~is set up~~ has a thickness, in terms of optical length, within ±30% of range of ~~a thickness of~~ an integral multiple of 1/4 of the oscillation wavelength of the semiconductor laser device.

15. (Currently Amended) The semiconductor laser device according to Claim 13, wherein the fifth dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3, and the sixth dielectric film is ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2.

16. (Currently Amended) The semiconductor laser device according to Claim 14, wherein the fifth dielectric film is ~~formed of either~~ selected from the group consisting of Al_2O_3, CeF_3, NdF_3, MgO, and Y_2O_3, and the sixth dielectric film is ~~formed of either~~ selected from the group consisting of SiO_2, MgF_2, BaF_2, and CaF_2.

17. (Currently Amended) The semiconductor laser device according to Claim 1, wherein the laser chip has a plurality of light emitting points which emit at least two ~~or more~~ different oscillation wavelengths.

18. (Currently Amended) The semiconductor laser device according to Claim 2, wherein the laser chip has a plurality of light emitting points which emit at least two ~~or more~~ different oscillation wavelengths.

19. (Currently Amended) The semiconductor laser device according to Claim 1, ~~wherein~~ including at least two ~~or more~~ of the semiconductor laser devices ~~are arranged~~ in a single package, ~~and each of~~ wherein the laser ~~chip emits~~ chips emit different oscillation ~~wavelength from each other~~ wavelengths, and each ~~of~~ multilayer dielectric film on the optical exit face of each laser chip is ~~formed of~~ the same material with the same thickness.

20. (Currently Amended) The semiconductor laser device according to Claim 2, ~~wherein~~ including at least two ~~or more~~ of the semiconductor laser devices ~~are arranged~~ in a single package, ~~and each of~~ wherein the laser ~~chip emits~~ chips emit different oscillation

~~wavelength from each other~~ wavelengths, and each ~~of~~ multilayer dielectric film on the optical exit face of each laser chip is ~~formed of~~ the same material with the same thickness.